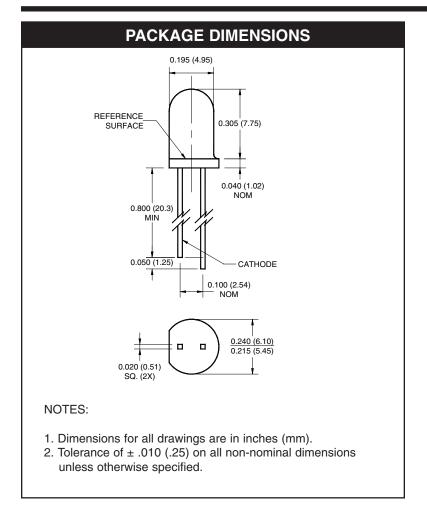
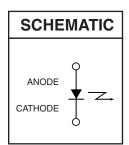
QED233 QED234







### **DESCRIPTION**

The QED233 / QED234 is a 940 nm GaAs / AlGaAs LED encapsulated in a clear untinted, plastic T-1 3/4 package.

### **FEATURES**

- λ= 940 nm
- Chip material =GaAs with AlGaAs window
- Package type: T-1 3/4 (5mm lens diameter)
- Matched Photosensor: QSD122/123/124
- Medium Emission Angle, 40°
- High Output Power
- Package material and color: Clear, untinted, plastic
- · Ideal for remote control applications



QED233 QED234

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise specified)								
Parameter	Symbol	Symbol Rating						
Operating Temperature	T <sub>OPR</sub>	-40 to +100	°C					
Storage Temperature	T <sub>STG</sub>	-40 to +100	°C					
Soldering Temperature (Iron)(2,3,4)	T <sub>SOL-I</sub>	240 for 5 sec	°C					
Soldering Temperature (Flow)(2,3)	T <sub>SOL-F</sub>	260 for 10 sec	°C					
Continuous Forward Current	I <sub>F</sub>	100	mA					
Reverse Voltage	V <sub>R</sub>	5	V					
Power Dissipation <sup>(1)</sup>	P <sub>D</sub>	200	mW					
Peak Forward Current	I <sub>FP</sub>	1.5	A					

- 1. Derate power dissipation linearly 2.67 mW/°C above 25°C.
- 2. RMA flux is recommended.
- 3. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 4. Soldering iron 1/16" (1.6mm) minimum from housing.
- 5. Pulse conditions;  $tp = 100 \mu s$ , T = 10 ms.

ELECTRICAL / OPTICAL CHARACTERISTICS (TA =25°C)									
PARAMETER	TEST CONDITIONS	DEVICE	SYMBOL	MIN	TYP	MAX	UNITS		
Peak Emission Wavelength	I <sub>F</sub> = 20 mA	ALL	$\lambda_{PE}$	_	940	_	nm		
Spectral Bandwidth	I <sub>F</sub> = 20 mA	ALL	_	50	_	nm			
Temp. Coefficient of $\lambda_{PE}$	I <sub>F</sub> = 100 mA	ALL	$TC_{\lambda}$	_	0.2	_	nm/K		
Emission Angle	I <sub>F</sub> = 100 mA	ALL	201/ <sub>2</sub>	_	40	_	Deg.		
Forward Voltage	$I_F = 100 \text{ mA}, \text{ tp} = 20 \text{ ms}$	ALL	V <sub>F</sub>	_	_	1.6	V		
Temp. Coefficient of V <sub>F</sub>	I <sub>F</sub> = 100 mA	ALL	TC <sub>V</sub>	_	-1.5	_	mV/K		
Reverse Current	V <sub>R</sub> = 5 V	ALL	I <sub>R</sub>	_	_	10	μA		
Radiant Intensity	$I_F = 100 \text{ mA}, \text{ tp} = 20 \text{ ms}$	QED233	I <sub>E</sub>	10	_	50	mW/sr		
		QED234		27	_	_			
Temp. Coefficient of I <sub>E</sub>	I <sub>F</sub> = 20 mA	ALL	TCı	_	-0.6	_	%/K		
Rise Time	I <sub>E</sub> = 100 mA	ALL	t <sub>r</sub>	_	1000	_	. ns		
Fall Time	1 <sub>F</sub> = 100 Hi/1	ALL	t <sub>f</sub>	_	1000	_			



QED233 QED234

### TYPICAL PERFORMANCE CURVES TBD

Fig. 1 Normalized Radiant Intensity vs. Forward Current

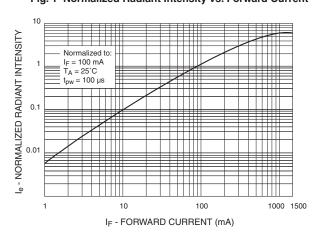


Fig. 2 Forward Voltage Vs. Ambient Temperature

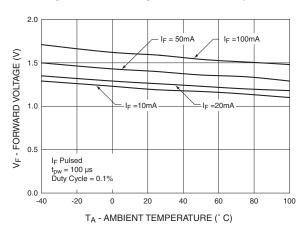


Fig. 3 Normalized Radiant Intensity vs. Wavelength

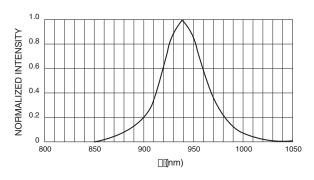


Fig. 4 Radiation Diagram

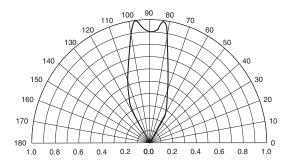
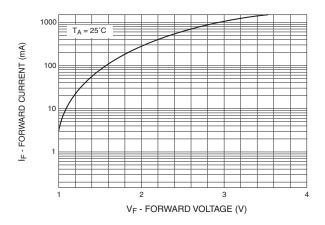


Fig. 5 Forward Current vs. Forward Voltage





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